

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	639753	(light near emitting near (device or diode or element)) or LED or (laser near2 diode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 19:47
L2	410231	substrate same (sapphire or SiC or (silicon near carbide) or Si or silicon or GaN or (gallium near nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 19:49
L3	41668	buffer near (layer or region)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 19:50
L4	6570	DBR or (distributed near bragg near reflector)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 19:51
L5	2944	(n-type near GaN) or n-GaN	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 19:52
L6	2704	p-GaN or (p-type near GaN)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 19:53
L7	21258	QW or (quantum near well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 19:53
L8	22124	QW or (quantum near well) or MQW	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 19:53
L9	67	I1 and I2 and I3 and I4 and I5 and I6 and I8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/02 19:54